



N 沟道增强型场效应晶体管
N-CHANNEL MOSFET

MC70N10A

主要参数 MAIN CHARACTERISTICS

ID	50A
V _{DSS}	100V
R _{dson-max} (@V _{gs} =10V)	13.5mΩ
Q _{g-typ}	27.8nC

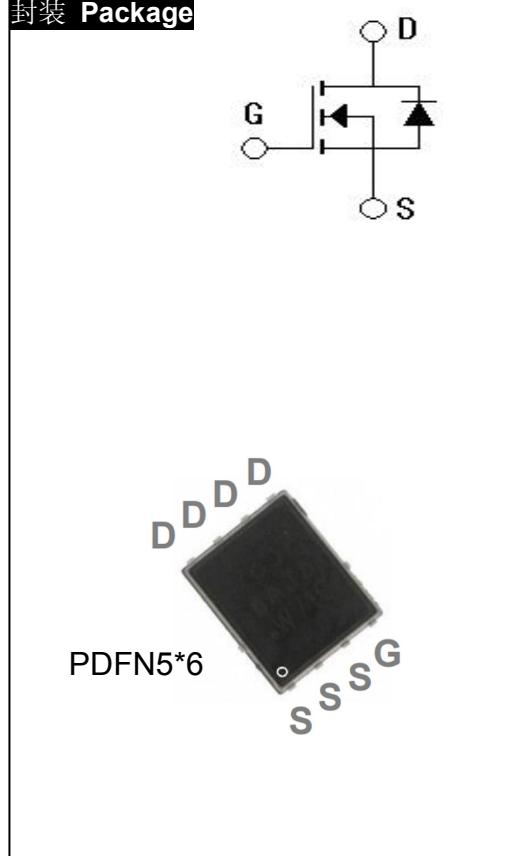
用途

- 电信与工业领域隔离 DC/DC 转换
- Isolated DC/DC Converters in Telecom and Industrial
- 同步整流领域 DC/DC 与 AC/DC 转换
- Synchronous Rectification in DC/DC and AC/DC Converters

产品特性

- 低栅极电荷
- 低 R_{dson}
- 开关速度快
- 产品全部经过雪崩测试
- 高抗 dv/dt 能力
- RoHS 产品
- Low gate charge
- Low R_{dson}
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS product

封装 Package



订货信息 ORDER MESSAGE

订货型号 Order codes				印记 Marking	封装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen-Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen-Free-Reel		
N/A	N/A	N/A	MC70N10A-AA-AR	MC70N10A	PDFN5*6



MC70N10A

绝对最大额定值 ABSOLUTE RATINGS (T_c=25°C)

项目 Parameter	符号 Symbol	数值 Value	单位 Unit
		MC70N10A	
最高漏极—源极直流电压 Drain-Source Voltage	V _{DSS}	100	V
连续漏极电流 Drain Current -continuous	I _D T=25°C	50*	A
	I _D T=100°C	40*	A
最大脉冲漏极电流 (注 1) Drain Current - pulse (note 1)	I _{DM}	200*	A
最高栅源电压 Gate-Source Voltage	V _{GSS}	+20/-12	V
单脉冲雪崩能量 (注 2) Single Pulsed Avalanche Energy (note 2)	E _{AS}	115	mJ
雪崩电流 (注 1) Avalanche Current (note 1)	I _{AS}	48	A
耗散功率 Power Dissipation	P _D T _c =25°C	62.5	W
	-Derate above 25°C	0.5	W/°C
最高结温及存储温度 Operating and Storage Temperature Range	T _J , T _{STG}	-55~+150	°C
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T _L	300	°C

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature



MC70N10A

电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最 小 Min	典 型 Typ	最 大 Max	单 位 Units
关态特性 Off -Characteristics						
漏—源击穿电压 Drain-Source Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	100	-	-	V
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V, T_C=25^\circ C$	-	-	1	μA
		$V_{DS}=80V, V_{GS}=0V, T_C=125^\circ C$	-	-	10	μA
正向栅极体漏电流 Gate-body leakage current, forward	I_{GSSF}	$V_{DS}=0V, V_{GS} = 20V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	I_{GSSR}	$V_{DS}=0V, V_{GS} = -12V$	-	-	-100	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	1.0	1.5	2.5	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D=20A$	-	11.4	13.5	$m\Omega$
		$V_{GS} = 4.5V, I_D=15A$	-	15.6	20	$m\Omega$
正向跨导 Forward Transconductance	g_{fs}	$V_{DS} = 10V, I_D=3A$ (note 4)	-	12	-	S
动态特性 Dynamic Characteristics						
栅电阻 Gate resistance	R_g	$V_{DS}=0V, V_{GS} = 0V, f=1.0MHz$	-	1.14	-	Ω
输入电容 Input capacitance	C_{iss}	$V_{DS}=50V, V_{GS} = 0V, f=1.0MHz$	-	1640	-	pF
输出电容 Output capacitance	C_{oss}		-	240	-	pF
反向传输电容 Reverse transfer capacitance	C_{rss}		-	4	-	pF



电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics							
延迟时间 Turn-On delay time	t _{d(on)}	V _{DD} =50V, I _D =1A, R _G =6.0Ω, V _{GS} =10V (note 3, 4)	-	14.2	-	ns	
上升时间 Turn-On rise time	t _r		-	20.8	-	ns	
延迟时间 Turn-Off delay time	t _{d(off)}		-	42	-	ns	
下降时间 Turn-Off Fall time	t _f		-	30	-	ns	
栅极电荷总量 Total Gate Charge	Q _g		-	27.8	-	nC	
栅—源电荷 Gate-Source charge	Q _{gs}		-	3.5	-	nC	
栅—漏电荷 Gate-Drain charge	Q _{gd}	V _{DS} =50V, I _D =10A V _{GS} =10V (note 3, 4)	-	8.8	-	nC	
漏—源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings							
正向最大连续电流	I _s	T _c =25°C	-	-	50	A	
Maximum Continuous Drain-Source Diode Forward Current							
正向最大脉冲电流	I _{SM}	T _c =25°C	-	-	200	A	
Maximum Pulsed Drain-Source Diode Forward Current							
正向压降	V _{SD}	T _J =25°C, V _{GS} =0V, I _s =1A	-	-	1.0	V	
Drain-Source Diode Forward Voltage							
反向恢复时间	t _{rr}	I _s =10A, T _J =25°C dI _F /dt=100A/μs (note 3)	-	43.5	-	ns	
Reverse recovery time			-	59.6	-	nC	
反向恢复电荷	Q _{rr}						
Reverse recovery charge							

热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	最 大 Max		单 位 Unit
		MC70N10A		
结到管壳的热阻 Thermal Resistance, Junction to Case	R _{th(j-c)}	2		°C/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	R _{th(j-A)}	75		°C/W

注释:

1: 脉冲宽度由最高结温限制

2: I_{AS}=48A, V_{DD}=50V, V_{GS}=10V, L=0.1mH, R_G=25Ω, 起始结温 T_J=25°C

3: 脉冲测试: 脉冲宽度≤300μs, 占空比≤2%

4: 基本与工作温度无关

Notes:

1: Pulse width limited by maximum junction temperature

2: I_{AS}=48A, V_{DD}=50V, V_{GS}=10V, L=0.1mH, R_G=25Ω, Starting T_J=25°C

3: Pulse Test: Pulse Width ≤300μs, Duty Cycle≤2%

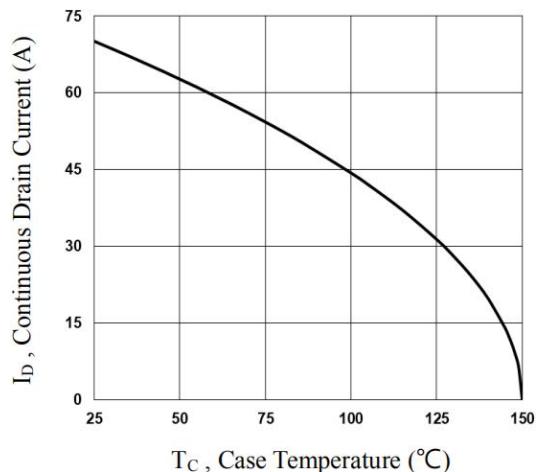
4: Essentially independent of operating temperature



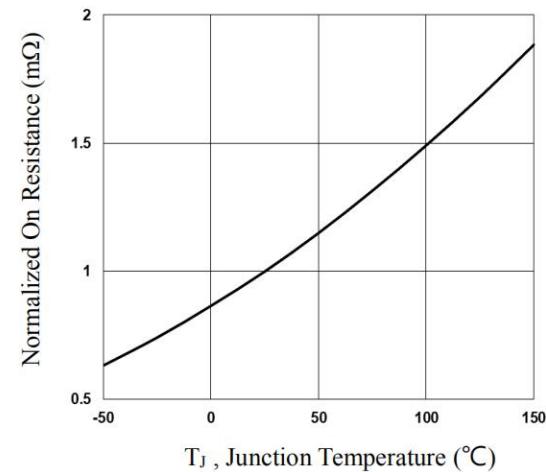
MC70N10A

特征曲线 ELECTRICAL CHARACTERISTICS (curves)

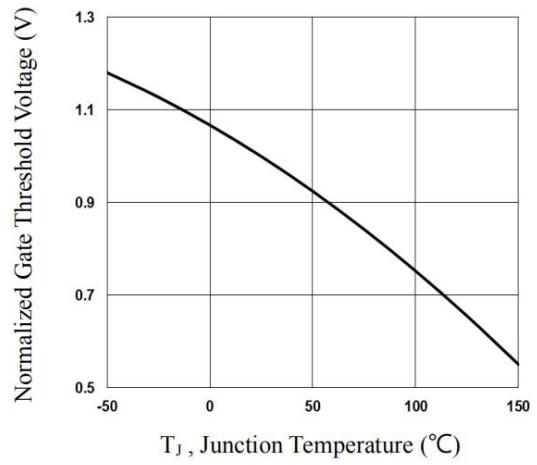
Drain Current Variation vs. Temperature



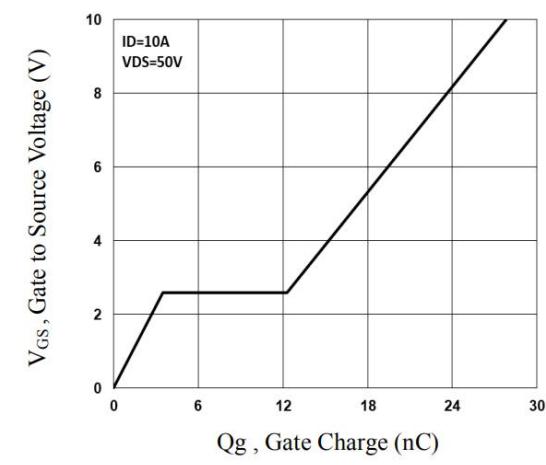
On-Resistance Variation vs. Temperature



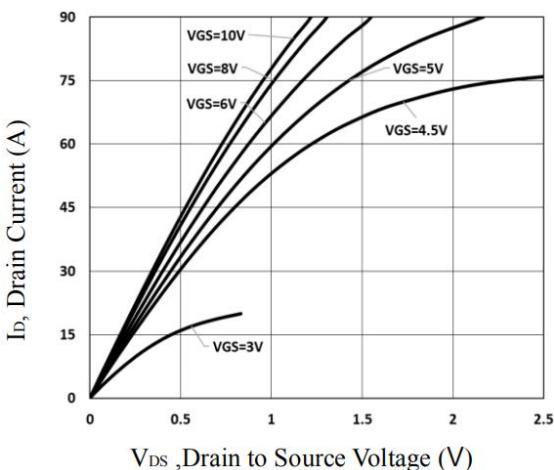
Gate Threshold Voltage Variation vs. Temperature



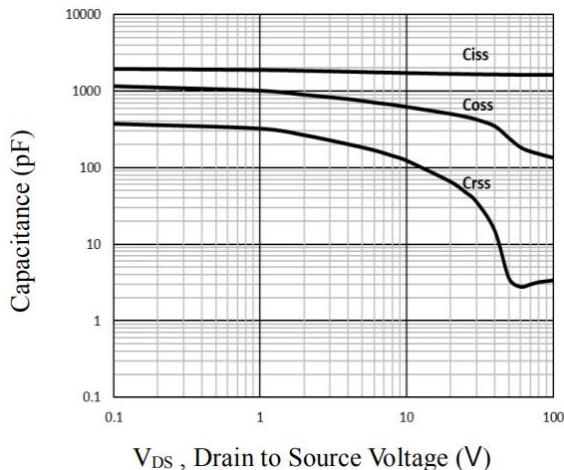
Gate Charge Characteristics



On-Region Characteristics



Capacitance Characteristics

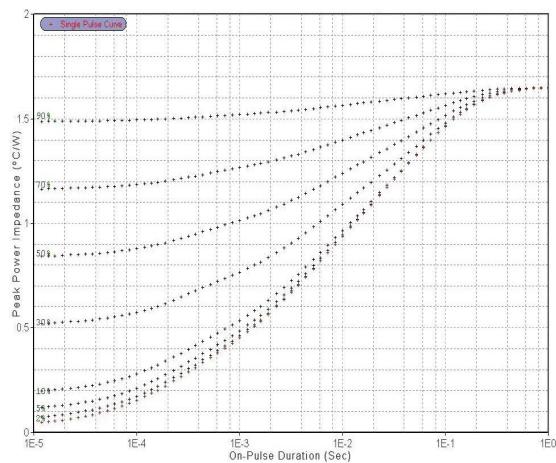




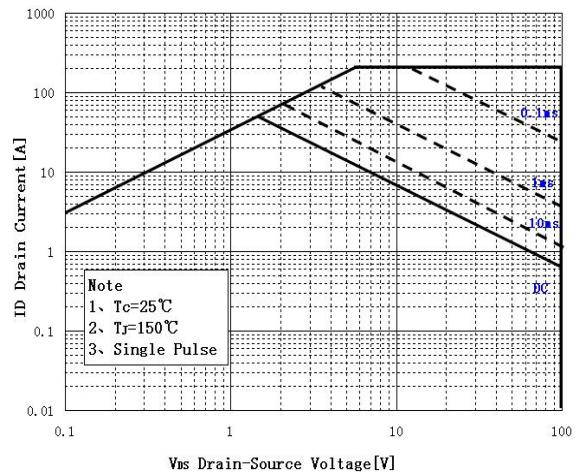
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特征曲线 ELECTRICAL CHARACTERISTICS (curves)

Transient Thermal Response Curve



Maximum Safe Operation Area



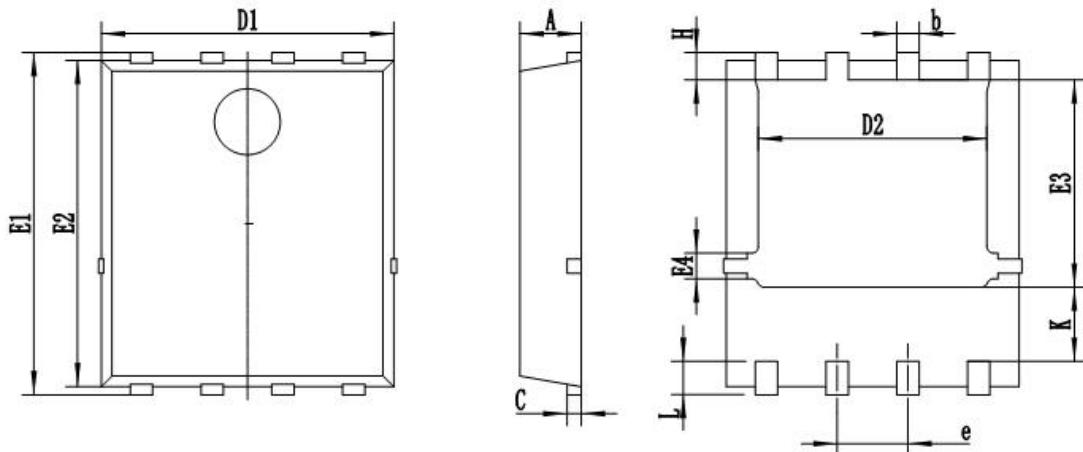


MC70N10A

外形尺寸 PACKAGE MECHANICAL DATA

PDFN5*6

单位 Unit: mm



SYMBOL	mm	
	MIN	MAX
A	0.95	1.25
C	0.1	0.4
b	0.25	0.55
D1	4.9	5.5
D2	3.75	4.3
e	1.27	BSC
E1	5.9	6.4
E2	5.6	6.1
E3	3.47	3.97
E4	0.31	0.61
L	0.25	0.75
H	0.35	0.65
K	1.13	1.53

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